



V_{RSM}, V_{RRM} V	V_{VRMS} V	$I_D = 30 \text{ A} (T_c = 94^\circ\text{C})$ Types	C_{max} μF	R_{min} Ω
200		SKB 30/02A1		0,15
400		SKB 30/04A1		0,3
800		SKB 30/08A1		0,5
1200		SKB 30/12A1		0,75
1400		SKB 30/14A1		0,9
1600		SKB 30/16A1		1

Power Bridge Rectifiers

SKB 30

Features

- Isolated metal case with screw terminals
- Blocking voltage up to 1600 V
- High surge current
- Easy chassis mounting
- UL recognized, file no. E 63 532

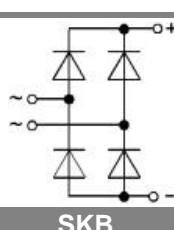
Typical Applications

- Single phase rectifiers for power supplies
- Input rectifiers for variable frequency drives
- Rectifiers for DC motor field supplies
- Battery charger rectifiers
- Recommended snubber network:
RC: 0.1 μF , 50 Ω ($P_R = 1 \text{ W}$)

1) Freely suspended or mounted on an insulator

2) Mounted on a painted metal sheet of min. 250 x 250 x 1 mm

Symbol	Conditions	Values	Units
I_D	$T_a = 45^\circ\text{C}$, isolated ¹⁾	6,5	A
	$T_a = 45^\circ\text{C}$, chassis ²⁾	15	A
I_{DCL}	$T_a = 45^\circ\text{C}$, isolated ¹⁾	6	A
	$T_a = 45^\circ\text{C}$, chassis ²⁾	13	A
I_{FSM}	$T_{vj} = 25^\circ\text{C}$, 10 ms	370	A
	$T_{vj} = 150^\circ\text{C}$, 10 ms	320	A
	i^2t $T_{vj} = 25^\circ\text{C}$, 8,3 ... 10 ms	680	A^2s
	$T_{vj} = 150^\circ\text{C}$, 8,3 ... 10 ms	500	A^2s
V_F	$T_{vj} = 25^\circ\text{C}$, $I_F = 150 \text{ A}$	max. 2,2	V
	$T_{vj} = 150^\circ\text{C}$	max. 0,85	V
r_T	$T_{vj} = 150^\circ\text{C}$	max. 12	$\text{m}\Omega$
I_{RD}	$T_{vj} = 25^\circ\text{C}$, $V_{RD}=V_{RRM}$	300	μA
	$T_{vj} = ^\circ\text{C}$, $V_{RD}=V_{RRM} \geq V$		μA
	$T_{vj} = 150^\circ\text{C}$, $V_{RD}=V_{RRM}$	5	mA
t_{rr}	$T_{vj} = ^\circ\text{C}$, $V_{RD}=V_{RRM} \geq V$		mA
	$T_{vj} = 25^\circ\text{C}$	25	μs
f_G		2000	Hz
$R_{th(j-a)}$	isolated ¹⁾	8,5	K/W
	chassis ²⁾	3,3	K/W
$R_{th(j-c)}$	total	0,7	K/W
	total	0,1	K/W
T_{vj}		- 40 ... + 150	$^\circ\text{C}$
		- 55 ... + 150	$^\circ\text{C}$
V_{isol}	a. c. 50 ... 60 Hz; r.m.s.; 1 s / 1 min.	3000 / 2500	V~
		5 \pm 15 %	Nm
M_s	to heatsink	1,5 \pm 15 %	Nm
	to terminals		m/s^2
M_t		125	g
a			
w			
F_u		25	A
Case		G 12	



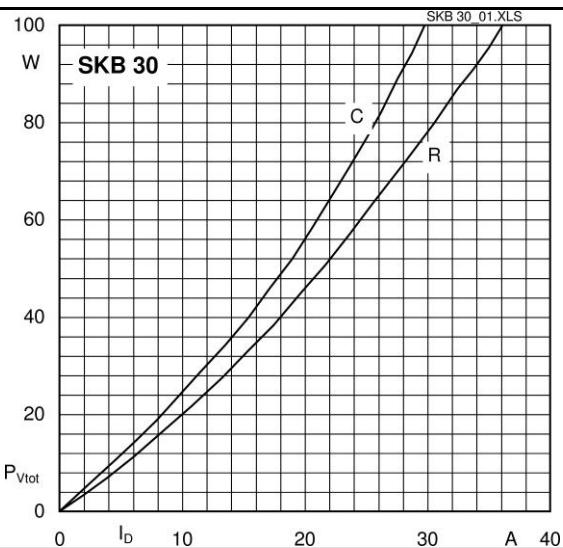


Fig. 3L Power dissipation vs. output current

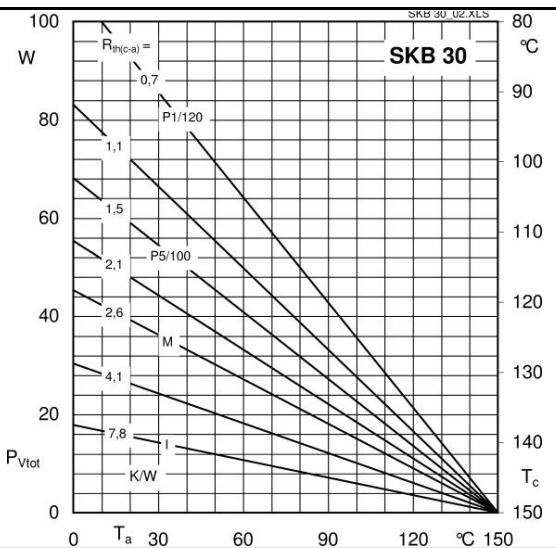


Fig. 3R Power dissipation vs. case temperature

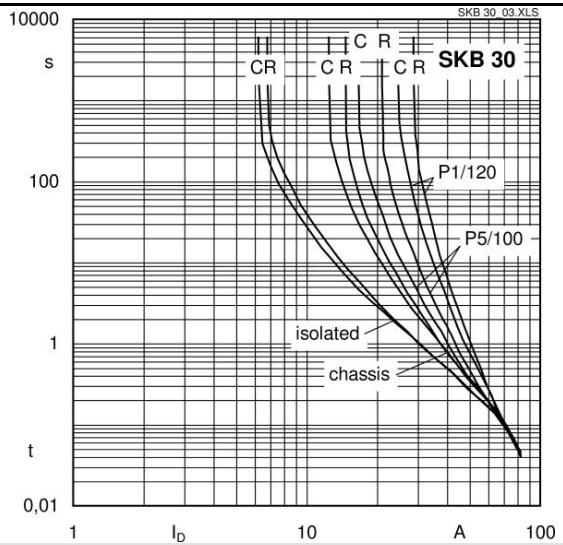


Fig. 6 Rated overload characteristics vs. time

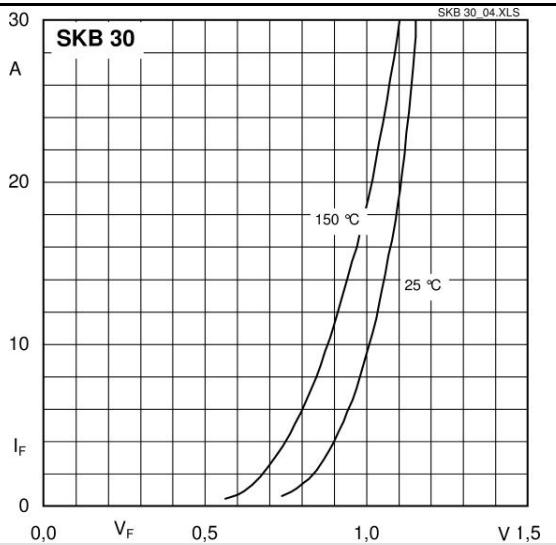
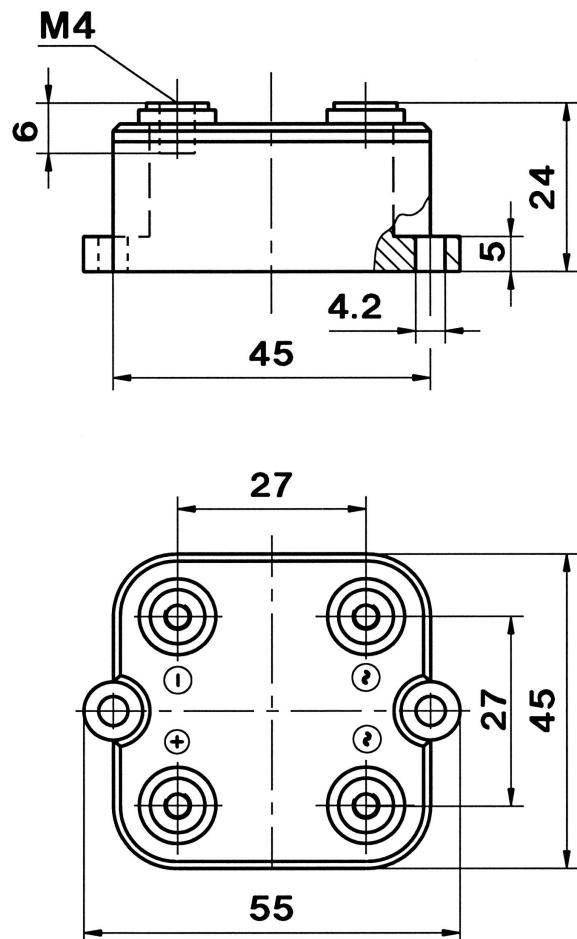


Fig. 9 Forward characteristics of a diode arm

Dimensions in mm



Case G 12

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